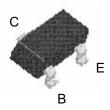


### FSB6726



SuperSOT™-3

# **PNP General Purpose Amplifier**

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.0 A. Sourced from Process 77.

# **Absolute Maximum Ratings\*** T<sub>A = 25°C unless otherwise noted</sub>

| Symbol                            | Parameter  | FSB660/FSB660A | Units |
|-----------------------------------|--|----------------|-------|
| V <sub>CEO</sub>                  | Collector-Emitter Voltage                        | 30             | V     |
| V <sub>CBO</sub>                  | Collector-Base Voltage                           | 40             | V     |
| V <sub>EBO</sub>                  | Emitter-Base Voltage                             | 5              | V     |
| Ic                                | Collector Current - Continuous                   | 1.5            | А     |
| T <sub>J</sub> , T <sub>stg</sub> | Operating and Storage Junction Temperature Range | -55 to +150    | °C    |

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Thermal Characteristics T<sub>A = 25°C unless otherwise noted</sub>

| Symbol            | Characteristic                          | Мах     | Units |
|-------------------|---|---------|-------|
|                   |   | FSB6726 |       |
| P <sub>D</sub>    | Total Device Dissipation                | 500     | mW    |
| R <sub>θ</sub> JA | Thermal Resistance, Junction to Ambient | 250     | °C/W  |

# **PNP General Purpose Amplifier**

(continued)

### **Electrical Characteristics**

T<sub>A</sub> = 25°C unless otherwise noted

| Symbol               | Parameter                            | Test Conditions                                       | Min | Max | Units |
|----------------------|--------------------------------------|---|-----|-----|-------|
| OFF CHA              | RACTERISTICS                         |   |     |     |       |
| BV <sub>CEO</sub>    | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> = 10 mA                                | 30  |     | V     |
| BV <sub>CBO</sub>    | Collector-Base Breakdown Voltage     | I <sub>C</sub> = 100 μA                               | 40  |     | V     |
| BV <sub>EBO</sub>    | Emitter-Base Breakdown Voltage       | I <sub>E</sub> = 100 μA                               | 5   |     | V     |
| I <sub>CBO</sub>     | Collector Cutoff Current             | V <sub>CB</sub> = 40 V                                |     | 100 | nA    |
| I <sub>EBO</sub>     | Emitter Cutoff Current               | V <sub>EB</sub> = 5V                                  |     | 100 | nA    |
| ON CHAR              | ACTERISTICS*                         |   |     |     |       |
| h <sub>FE</sub>      | DC Current Gain                      | I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 1 V        | 60  |     | -     |
|                      |                                      | $I_C = 1 A$ , $V_{CE} = 1V$                           | 50  | 250 | -     |
| V <sub>CE(sat)</sub> | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 1 A, I <sub>B</sub> = 100 mA         |     | 500 | mV    |
| V <sub>BE(on)</sub>  | Base-Emitter On Voltage              | I <sub>C</sub> = 1 A, V <sub>CE</sub> = 1 V           |     | 1.2 | V     |
| SMALL S              | IGNAL CHARACTERISTICS                |   | •   |     |       |
| C <sub>cb</sub>      | Collector-Base Capacitance           | V <sub>CB</sub> = 10 V, f = 1MHz                      |     | 30  | pF    |
| hfe                  | Small Signal Current Gain            | I <sub>C</sub> = 50 mA,V <sub>CE</sub> = 10V, f=20MHz | 2.5 | 25  | -     |

\*Pulse Test: Pulse Width  $\leq 300~\mu\text{s},~\text{Duty Cycle} \leq 2.0\%$ 

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E<sup>2</sup>CMOS<sup>™</sup> PowerTrench<sup>™</sup>

FACT™ QS™

 $\begin{array}{lll} \mathsf{FACT} \ \mathsf{Quiet} \ \mathsf{Series}^\mathsf{TM} & \mathsf{Quiet} \ \mathsf{Series}^\mathsf{TM} \\ \mathsf{FAST}^{\mathbb{R}} & \mathsf{SuperSOT}^\mathsf{TM}\text{-}3 \\ \mathsf{FASTr}^\mathsf{TM} & \mathsf{SuperSOT}^\mathsf{TM}\text{-}6 \\ \mathsf{GTO}^\mathsf{TM} & \mathsf{SuperSOT}^\mathsf{TM}\text{-}8 \\ \mathsf{HiSeC}^\mathsf{TM} & \mathsf{TinyLogic}^\mathsf{TM} \\ \end{array}$ 

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### PRODUCT STATUS DEFINITIONS

### **Definition of Terms**

| Datasheet Identification | Product Status            | Definition  |
|--------------------------|---------------------------|---|
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| No Identification Needed | Full Production           | This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.   |
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